L Number	Hits	Search Text	DB	Time stamp
1	496	(((257/13-15' or (257/79-103)).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:12
2	112	@ad<=20000203 and 'GaN' and 'n-type electrode' same 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:14
3	46	@ad<=20000203 and 'GaN' and 'n-type electrode' same 'thickness'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:24
4	3	@ad<=20000203 and 'GaN' and 'thin' with 'n-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:26
5	2	(@ad<=20000203 and 'GaN' and 'thin' with 'n-type electrode') and thickness near3 (nm nanometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:28
6	25	@ad<=20000203 and 'GaN' and electrode near3 thickness near3 (nm nanometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:39
7	1	@ad<=20000203 and 'GaN' and electrode near3 thickness near3 '30'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:33
8	40	@ad<=20000203 and 'GaN' same 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:35
9	2	@ad<=20000203 and 'GaN' same 'transparent' with 'n type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:36
10	116	@ad<=20000203 and 'GaN' and 'n' with 'electrode' same '50'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:40
11	33	@ad<=20000203 and 'GaN' and 'n' near2 'electrode' with '50'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:40
12	10	@ad<=20000203 and 'GaN' and 'n' near2 'electrode' with '50 nm'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:40
13	19	@ad<=20000203 and 'GaN' and 'n' with 'electrode' with '50 nm'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:47
14	10	@ad<=20000203 and 'GaN' and 'n' adj2 'electrode' with '50 nm'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:48

-	507	(257/21).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 13:01
-	16	((257/21).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:53
-	107	@ad<=20000203 and 'GaN' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:28
-	1	@ad<=20000203 and 'GaN' and 'n-type electrode' and 'p-type electrode' with 'pad'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 07:59
-	2	("6172382").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 13:44
-	16	((257/21).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 16:46
-	273	@ad<=20000203 and 'GaN' and 'electrode' with 'transparent'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:26
-	3	@ad<=20000203 and 'GaN' and 'n-type electrode' and 'p-type electrode' with 'transparent'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 09:56
-	0	@ad<=20000203 and 'GaN' and 'n-type electrode' with 'trans'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:01
-	2	@ad<=20000203 and 'GaN' and 'n-type electrode' with 'transmissive'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:01
-	7	@ad<=20000203 and 'GaN' and 'transmissive electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:06
-	996	(257/59).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:53
-	0	("103 and 'GaN'").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:14
-	6	((257/59).CCLS.) and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:23

-	837	(257/72).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:53
-	2	((257/72).CCLS.) and 'GaN' and 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:24
-	166	@ad<=20000203 and 'GaN' and 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:27
-	115	@ad<=20000203 and 'GaN' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:11
-	16	((257/21).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:53
-	1128	(257/59).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:54
-	957	(257/72).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:54
-	560	(438/22).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 11:05
-	1108	((438/22) or (257/79)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 11:07
-	106	@ad<=20000203 and 'GaN' and 'n-type' and 'p-type' and 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 12:03
-	35	@ad<=20000203 and 'GaN' and 'n-type' same 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 13:48
-	7979	((257/13-15) or (257/79-103)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 13:48
-	463	(((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:03
-	709	(438/22-24).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 13:50

-	0	@ad<=20000203 and 'light emitting diode' and 'n-type electrode' with 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 15:58
-	244	@ad<=20000203 and 'light emitting diode' and 'n-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 15:47
-	13	(@ad<=20000203 and 'light emitting diode' and 'n-type electrode') and ITO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 15:48
-	0	@ad<=20000203 and 'n-type electrode' with 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 15:58
-	0	@ad<=20000203 and 'n-type electrode' near 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 15:59
-	55	@ad<=20000203 and 'n-type electrode' and 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:03
-	1	@ad<=20000203 and 'n-type electrode' and 'TCO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:05
-	49	@ad<=20000203 and 'LED' and 'transmissive electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:06
-	8	@ad<=20000203 and 'GaN' and 'transmissive electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:07
-	1197	@ad<=20000203 and (257/98).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:52
-	145	@ad<=20000203 and (257/91).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:52
-	655	@ad<=20000203 and (257/94).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:53
-	925	@ad<=20000203 and (257/103).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:53
-	1315	@ad<=20000203 and (257/99).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:54

~	2	("6100545").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:54	
~	7	@ad<=20000203 and 'GaN' with 'transparent' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:56	
~	22	@ad<=20000203 and 'GaN' and 'transparent' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:29	
~	8	@ad<=20000203 and 'GaN' and 'transparent' same 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:39	
~	24	@ad<=20000203 and 'GaN' with 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:40	
~	16	@ad<=20000203 and 'Gallium nitride' with 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:40	
~	26	@ad<=20000203 and 'GaN' and 'n-type' with 'p-type' same 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:57	
~	0	@ad<=20000203 and 'GaN' and 'n-type transparent electrode' same 'p-type transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:58	
~	0	@ad<=20000203 and 'n-type transparent electrode' same 'p-type transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:59	
~	486	(((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:11	
~	314	(((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'gallium nitride'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:04	
~	2	"20010042860"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 13:01	